

P27127.P10 Received 05/09/2006

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FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. P27127	Application No. 10/707,840
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant Huilong ZHU et al.			
		Filing Date January 16, 2004		Group <del>2814</del> 2818	

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EXAMINER	/Dao Nguyen/	DATE CONSIDERED	01/08/2007
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			

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U.S. PATENT DOCUMENTS					
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS    SUBCLASS
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